



## NPN Power Silicon Transistor

*Qualified per MIL-PRF-19500/315*

*Qualified Levels:  
JAN, JANTX, and  
JANTXV*

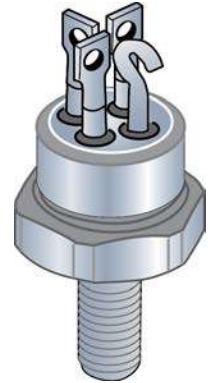
### DESCRIPTION

This NPN silicon transistor is rated at 5 amps and is military qualified up to the JANTXV level. This TO-111 isolated package features a 180 degree lead orientation.

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- JEDEC registered 2N3749
- Low saturation voltage
- Low leakage current
- Fast switching capable - 0.5  $\mu$ s rise time
- High frequency response
- TO-111 case with isolated terminals
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/315
- RoHS compliant versions available (commercial grade only)



**TO-111 Package**

### APPLICATIONS / BENEFITS

- Class 3B to ESD per MIL-STD-750 Method 1020
- High frequency inverters
- Converters
- Linear amplifiers
- High speed switching regulated power supplies
- RF power supplies

### MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value	Unit	
Junction and Storage Temperature	$T_J$ and $T_{STG}$	-65 to +200	$^{\circ}C$	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	3.33	$^{\circ}C/W$	
Collector Current	$I_C$	5.0	A	
Collector-Emitter Voltage	$V_{CEO}$	80	V	
Collector-Base Voltage	$V_{CBO}$	110	V	
Emitter-Base Voltage	$V_{EBO}$	8.0	V	
Total Power Dissipation	$P_T$	@ $T_A = +25^{\circ}C$ <sup>(1)</sup>	2.0	W
		@ $T_C = +100^{\circ}C$ <sup>(2)</sup>	30	

- Notes:**
1. Derate linearly 11.4 mW/ $^{\circ}C$  for  $T_A > +25^{\circ}C$ .
  2. Derate linearly 300 mW/ $^{\circ}C$  for  $T_C > +100^{\circ}C$ .

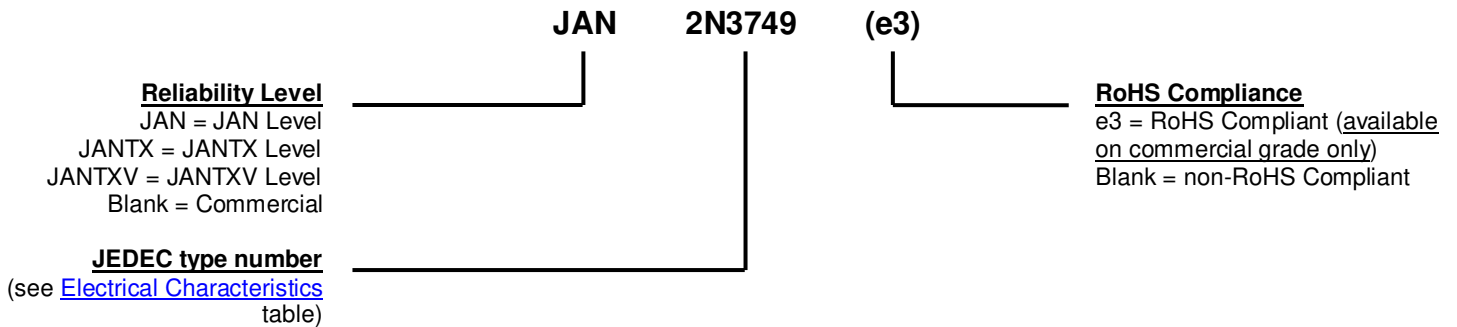
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**MECHANICAL and PACKAGING**

- CASE: Nickel Plated
- TERMINALS: Solder Dip over Nickel Plating. RoHS compliant Matte/Tin available on commercial grade only.
- MARKING: Manufacturer's ID, Date Code, Part Number, BeO
- POLARITY: See Package Outline Drawing on last page
- WEIGHT: Approximately 5.412 grams
- See [Package Dimensions](#) on last page.

**PART NOMENCLATURE**

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$I_B$	Base current: The value of the dc current into the base terminal.
$I_C$	Collector current: The value of the dc current into the collector terminal.
$I_E$	Emitter current: The value of the dc current into the emitter terminal.
$P_T$	Total power dissipation: The sum of the forward and reverse power dissipations.
$V_{BE}$	Base-emitter voltage: The dc voltage between the base and the emitter.
$V_{CE}$	Collector-emitter voltage: The dc voltage between the collector and the emitter.
$V_{CEO}$	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.
$V_{CB}$	Collector-base voltage: The dc voltage between the collector and the base.
$V_{CBO}$	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.
$V_{EB}$	Emitter-base voltage: The dc voltage between the emitter and the base
$V_{EBO}$	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.

**ELECTRICAL CHARACTERISTICS @  $T_C = 25^\circ\text{C}$  unless otherwise noted**

Characteristic	Symbol	Min.	Max.	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage $I_C = 100\text{ mA}$	$V_{(BR)CEO}$	80		V
Collector-Emitter Breakdown Voltage $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	110		V
Emitter-Base Breakdown to Voltage $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	8.0		V
Collector-Emitter Cutoff Current $V_{CE} = 60\text{ V}$	$I_{CEO}$		20	$\mu\text{A}$
Collector-Base Cutoff Current $V_{CB} = 80\text{ V}$	$I_{CBO}$		0.2	$\mu\text{A}$
Collector-Emitter Cutoff Current $V_{CE} = 110\text{ V}, V_{BE} = -0.5$	$I_{CEX}$		1.0	$\mu\text{A}$
Emitter-Base Cutoff Current $V_{EB} = 6.0\text{ V}$	$I_{EBO}$		0.2	$\mu\text{A}$

**ON CHARACTERISTICS**

Forward-Current Transfer Ratio $I_C = 50\text{ mA}, V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}, V_{CE} = 2.0\text{ V}$ $I_C = 5.0\text{ A}, V_{CE} = 5.0\text{ V}$	$h_{FE}$	40 40 15	120 120	
Base-Emitter Voltage Non-saturated $V_{CE} = 2.0\text{ V}, I_C = 1.0\text{ A}$	$V_{BE}$		1.2	V
Collector-Emitter Saturation Voltage $I_C = 1.0\text{ A}, I_B = 0.1\text{ A}$ $I_C = 5.0\text{ A}, I_B = 0.5\text{ A}$	$V_{CE(sat)}$		0.25 1.5	V
Base-Emitter Saturation Voltage $I_C = 1.0\text{ A}, I_B = 0.1\text{ A}$	$V_{BE(sat)}$		1.2	V

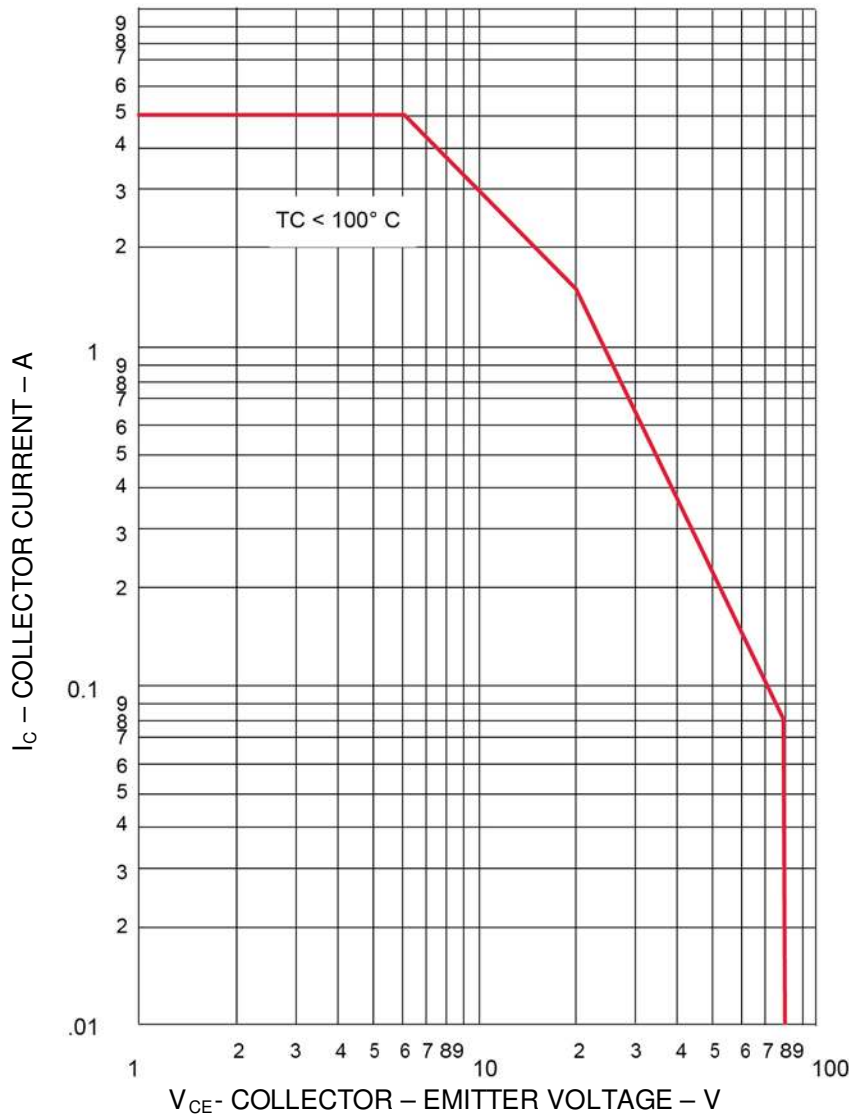
**DYNAMIC CHARACTERISTICS**

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0\text{ A}, V_{CE} = 10.0\text{ V}, f = 10\text{ MHz}$	$ h_{fe} $	3.0	12	
Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 50\text{ mA}, V_{CE} = 5.0\text{ V}, f = 1\text{ kHz}$	$h_{fe}$	40	140	
Output Capacitance $V_{CB} = 10\text{ V}, I_E = 0, 100 \leq f \leq 1.0\text{ MHz}$	$C_{obo}$		150	pF

**SWITCHING CHARACTERISTICS**

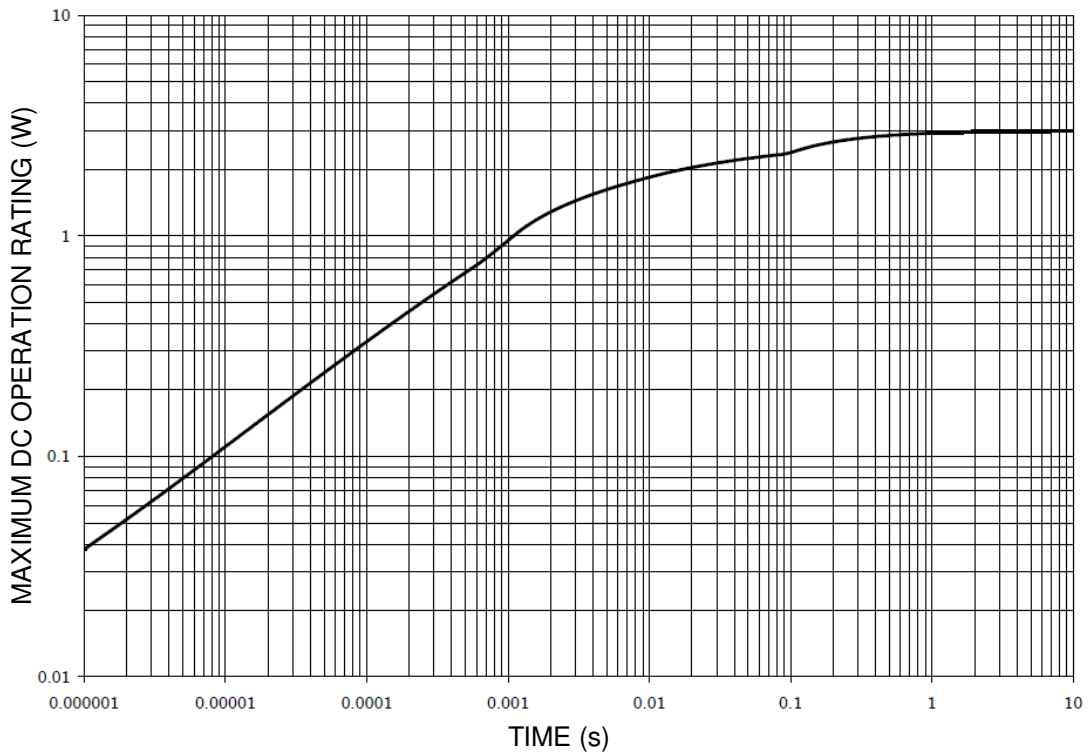
Pulse delay time	$t_d$		60	ns
Pulse rise time	$t_r$		300	ns
Pulse storage time	$t_s$		1.7	$\mu\text{s}$
Pulse fall time	$t_f$		300	ns

**ELECTRICAL CHARACTERISTICS @  $T_C = 25^\circ\text{C}$  unless otherwise noted. (continued)**
**SAFE OPERATING AREA (See Figure below and [MIL-STD-750, Test Method 3053](#))**
**DC Tests**
 $T_C = +100^\circ\text{C}$ ,  $t = 10$  seconds

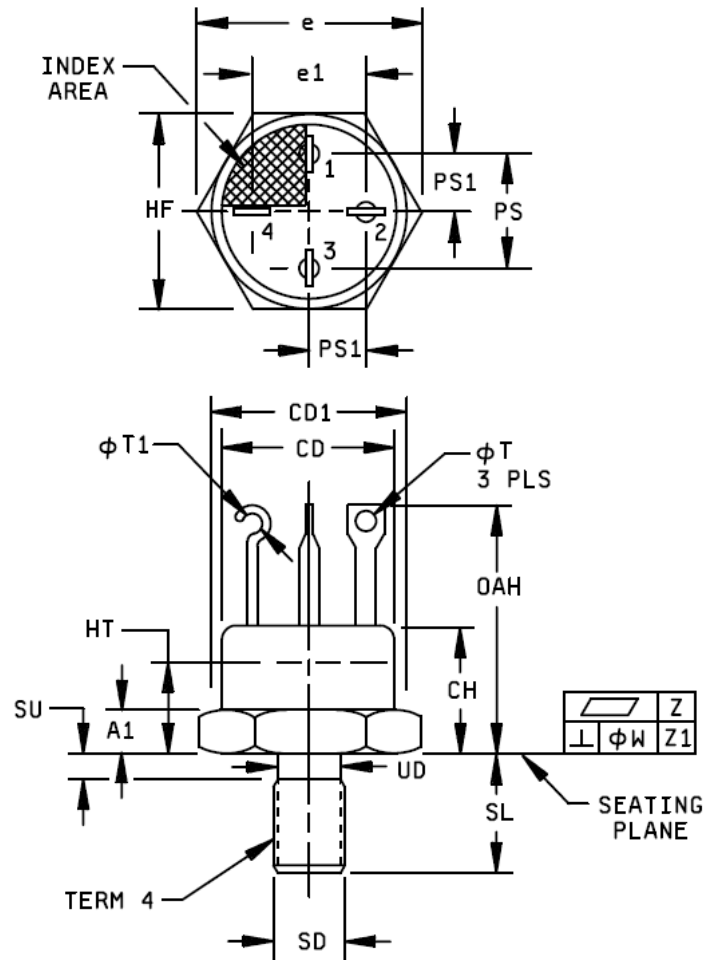
**Test 1**
 $V_{CE} = 80\text{ V}$ ,  $I_C = 80\text{ mA}$ 
**Test 2**
 $V_{CE} = 20\text{ V}$ ,  $I_C = 1.5\text{ A}$ 


**FIGURE 1**  
Maximum Safe Operating Area

GRAPHS



**FIGURE 2**  
Thermal Impedance

**PACKAGE DIMENSIONS**

**NOTES:**

1. Dimensions are in inches.
2. Millimeters are given for information only.
3. Terminal 1 - emitter; terminal 2 - base; terminal 3 - collector; terminal 4 - case.
4. Chamfer or undercut on one, or both, ends of hexagonal portion is optional.
5. The outline contour, with the exception of the hexagon, is optional within cylinder defined by  $CD1$  and  $HT$ .
6. Terminal 4 can be flattened and pierced or hook type. A visual index is required when the flattened and pierced tab terminal contour (identical to the adjacent terminals) option is used.
7. Angular orientation of terminals with respect to hexagon is optional.
8.  $A1$  dimension does not include sealing flanges.
9.  $SU$  is the length of incomplete or undercut threads.
10.  $SD$  is the outer diameter of coated threads. (Reference: Screw thread standards for Federal Standard H28/1, (FED-STD-H28/1))

Symbol	Dimension				Notes
	Inch		Millimeters		
	Min	Max	Min	Max	
<b>CH</b>	0.0320	0.458	8.13	11.63	
<b>HT</b>	-	0.250	-	6.35	5
<b>CD</b>	0.318	0.380	8.08	9.65	
<b>CD1</b>	0.380	0.437	9.65	11.10	5
<b>HF</b>	0.423	0.438	10.74	11.13	
<b>E</b>	-	0.505	-	12.83	
<b>E1</b>	0.180	0.215	4.57	5.46	7
<b>A1</b>	0.090	0.0150	2.29	3.81	4, 8
<b>OAH</b>	0.570	0.763	14.48	19.38	
<b>SL</b>	0.400	0.0455	10.16	11.56	
<b>SU</b>	-	0.078	-	1.98	9
$\phi T$	0.040	0.065	1.02	1.65	
$\phi T1$	0.040	0.070	1.02	1.78	6
<b>SD</b>	0.190-32UNF-2A				10
<b>Z</b>	-	0.02	-	0.05	
<b>Z1</b>	-	0.006	-	0.15	